Schottky barrier diode

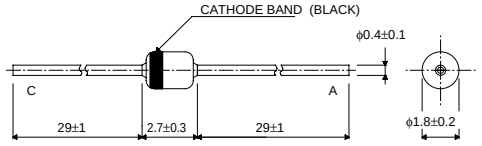
RB441Q-40

●Applications
Low current rectification

●Features
1) Glass sealed envelope for high reliability. (MSD)
2) Small pitch enables insertion on PCBs.
3) Low V_F.(V_F=0.45V Typ. at 100mA)

●Construction
Silicon epitaxial planar

●External dimensions (Units : mm)



ROHM : MSD
EIAJ : –
JEDEC : DO-34

Product identification number "S3" is stamped on body of main unit.

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	0.1	A
Peak forward surge current	I_{FSM}	1	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−40~+125	°C

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	–	–	0.34	V	I_F=10mA
Forward voltage	V_{F2}	–	–	0.55	V	I_F=100mA
Reverse current	I_R	–	–	100	μA	V_R=40V
Capacitance between terminals	C_T	–	6.0	–	pF	V_R=10V, f=1MHz

Note) ESD sensitve product handling required.

●**Electrical characteristic curves** (Ta = 25°C)

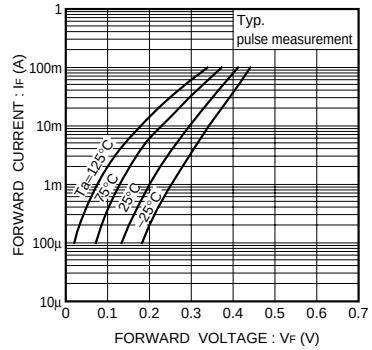


Fig. 1 Forward characteristics

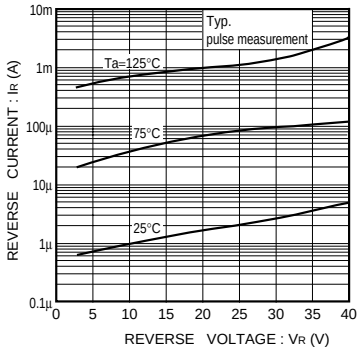


Fig. 2 Reverse characteristics

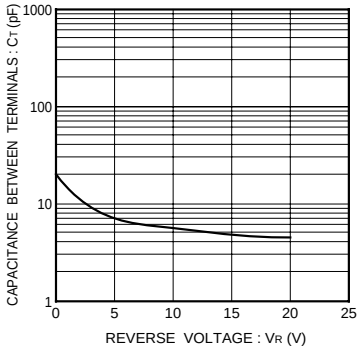


Fig. 3 Capacitance between terminals characteristics

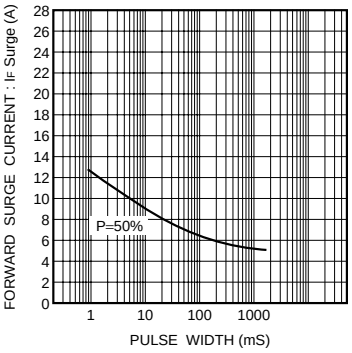


Fig. 4 Forward surge current characteristics

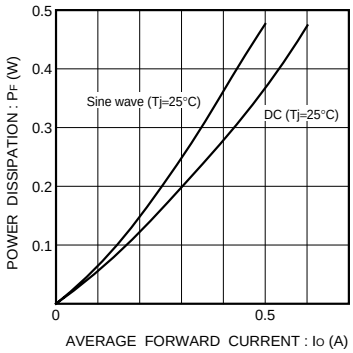


Fig. 5 Mean rectifying current characteristics

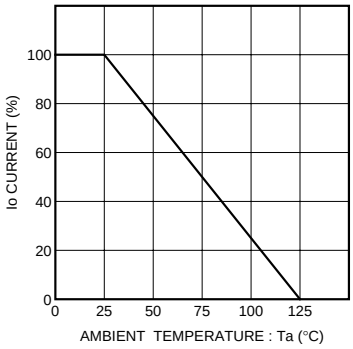


Fig. 6 Derating curve (mounting on glass epoxy PCBs)